

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (U-MOS II)

2SK2985

HIGH CURRENT SWITCHING APPLICATIONS

DC-DC CONVERTER, RELAY DRIVE AND MOTOR DRIVE APPLICATIONS

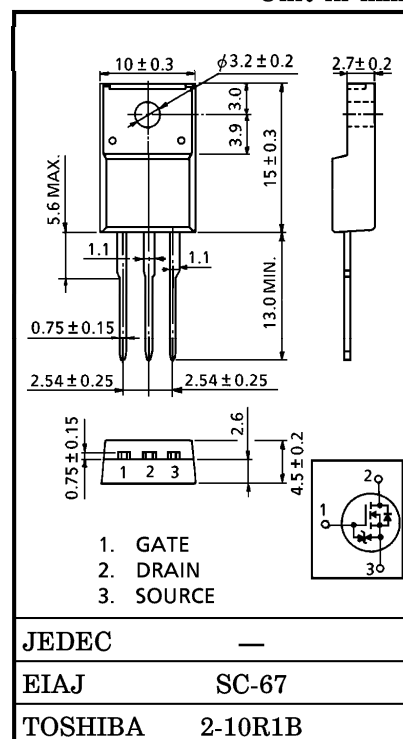
INDUSTRIAL APPLICATIONS

Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 4.5 \text{ m}\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 70 \text{ S}$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100 \mu\text{A}$ (Max.) ($V_{DS} = 60 \text{ V}$)
- Enhancement-Mode : $V_{th} = 1.3 \sim 2.5 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage ($R_{GS} = 20 \text{ k}\Omega$)	V_{DGR}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	DC	I_D	A
	Pulse	I_{DP}	
Drain Power Dissipation ($T_c = 25^\circ\text{C}$)	P_D	45	W
Single Pulse Avalanche Energy**	E_{AS}	701	mJ
Avalanche Current	I_{AR}	45	A
Repetitive Avalanche Energy*	E_{AR}	4.5	mJ
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ\text{C}$



Weight 1.9 g

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	2.78	$^\circ\text{C/W}$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	62.5	$^\circ\text{C/W}$

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

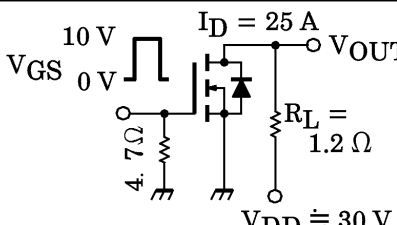
** $V_{DD} = 25 \text{ V}$, Starting $T_{ch} = 25^\circ\text{C}$, $L = 471 \mu\text{H}$,
 $I_{AR} = 45 \text{ A}$, $R_G = 25 \Omega$

This transistor is an electrostatic sensitive device.
Please handle with caution.

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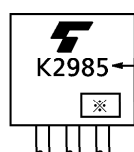
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	—	—	±10	μA
Drain Cut-off Current		I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	—	—	100	μA
Drain-Source Breakdown Voltage	V _(BR) DSS	I _D = 10 mA, V _{GS} = 0 V	60	—	—	V	
	V _(BR) DSX	I _D = 10 mA, V _{GS} = −20 V	40	—	—		
Gate Threshold Voltage		V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.3	—	2.5	V
Drain-Source ON Resistance		R _{DS} (ON)	V _{GS} = 10 V, I _D = 25 A	—	4.5	5.8	mΩ
			V _{GS} = 4 V, I _D = 25 A	—	5.8	10	
Forward Transfer Admittance		Y _{fs}	V _{DS} = 10 V, I _D = 25 A	35	70	—	S
Input Capacitance		C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	—	9300	—	pF
Reverse Transfer Capacitance		C _{rss}		—	910	—	
Output Capacitance		C _{oss}		—	1435	—	
Switching Time	Rise Time	t _r		—	18	—	ns
	Turn-on Time	t _{on}		—	50	—	
	Fall Time	t _f		—	110	—	
	Turn-off Time	t _{off}		V _{IN} : t _r , t _f < 5 ns Duty ≤ 1%, t _w = 10 μs	—	480	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q _g	V _{DD} ≐ 48 V, V _{GS} = 10 V, I _D = 45 A	—	210	—	nC
Gate-Source Charge		Q _{gs}		—	145	—	
Gate-Drain (“Miller”) Charge		Q _{gd}		—	65	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	45	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	180	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 45 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.5	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 45 \text{ A}, V_{GS} = 0 \text{ V}$	—	60	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR}/dt = 50 \text{ A}/\mu\text{s}$	—	50	—	nC

MARKING



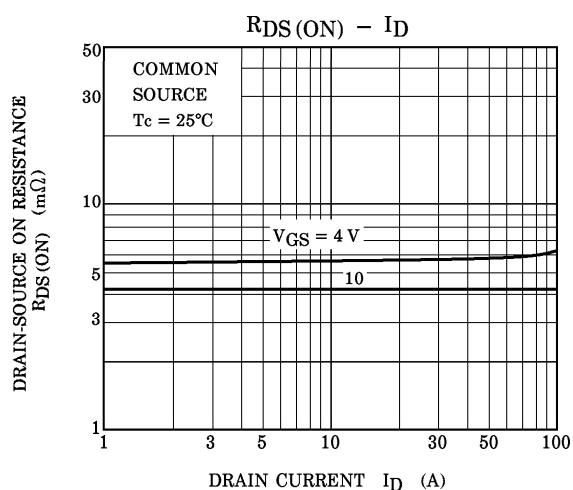
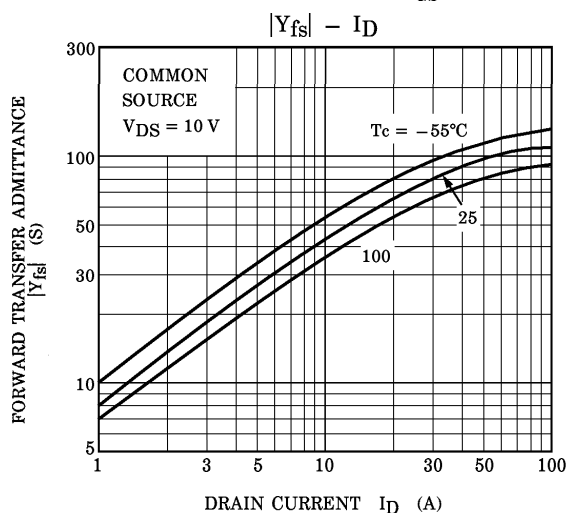
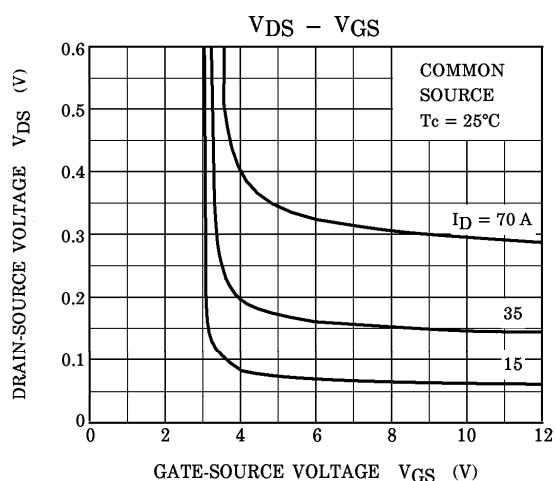
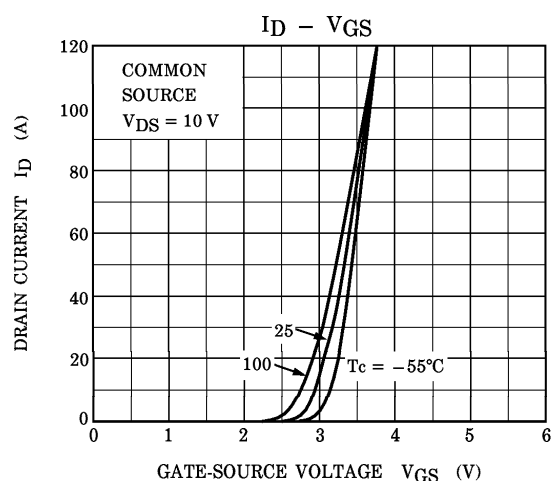
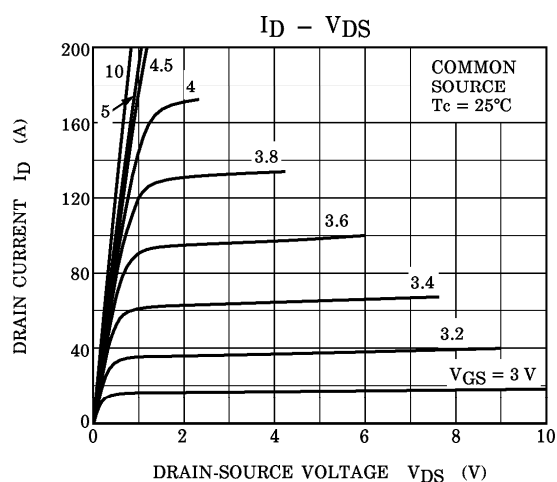
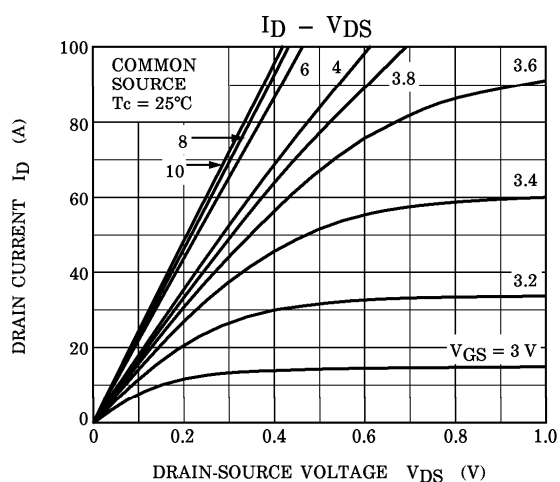
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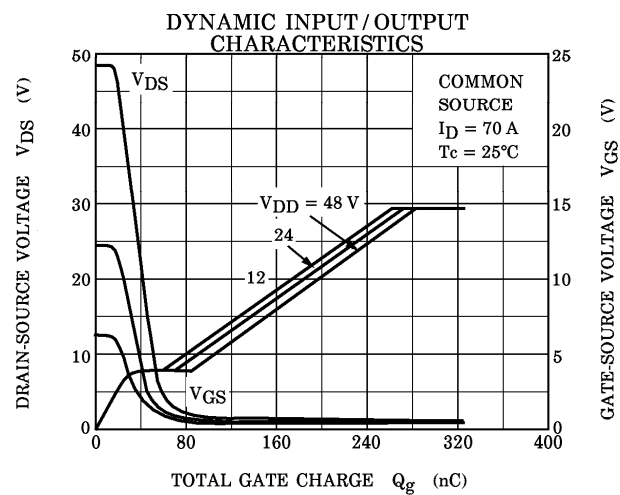
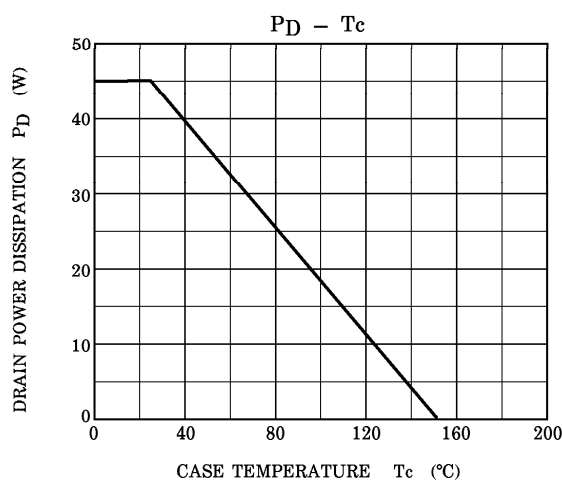
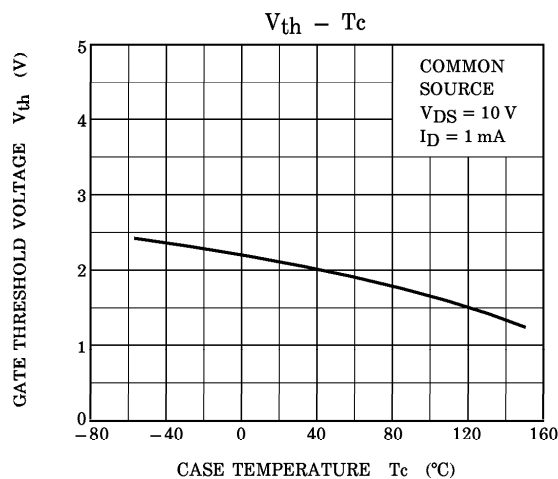
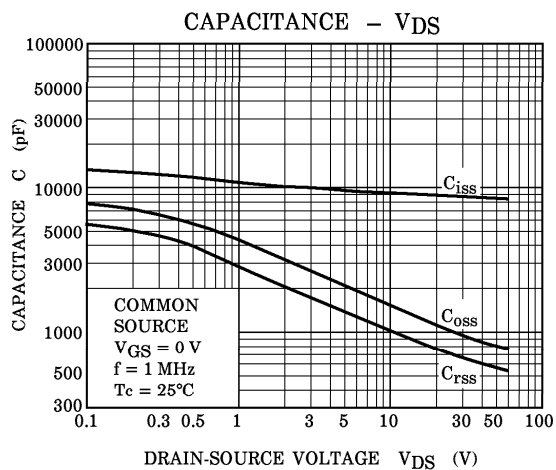
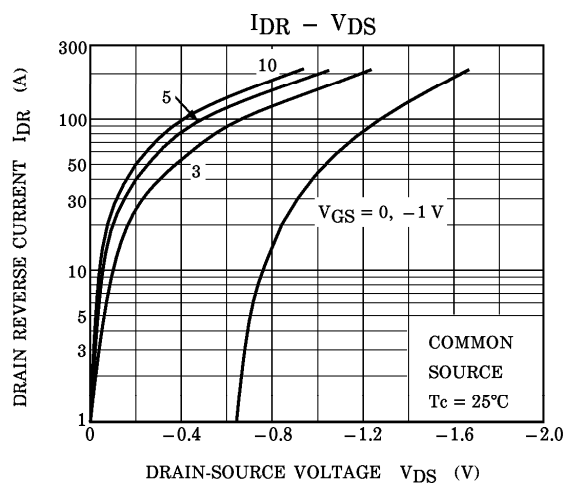
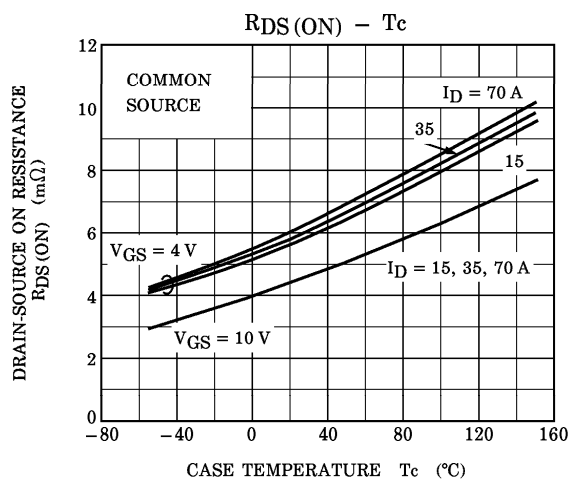
※ Lot Number

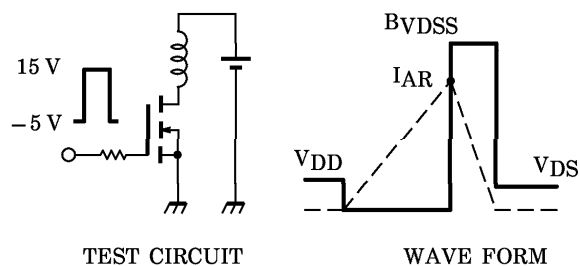
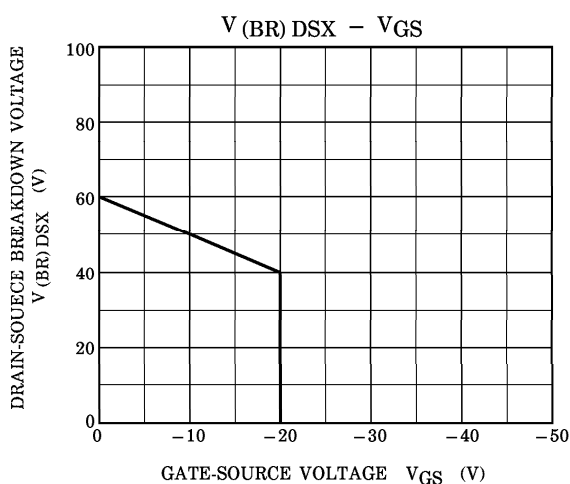
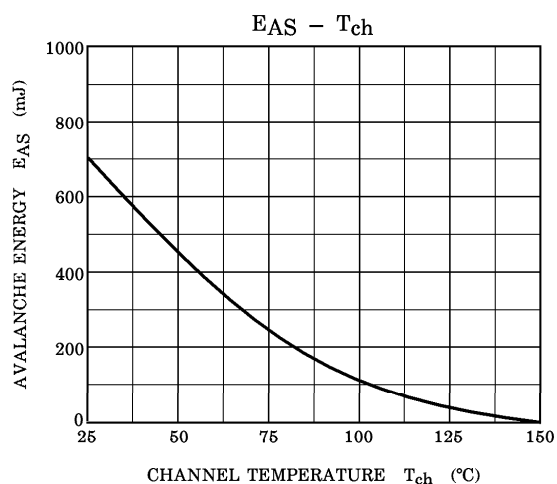
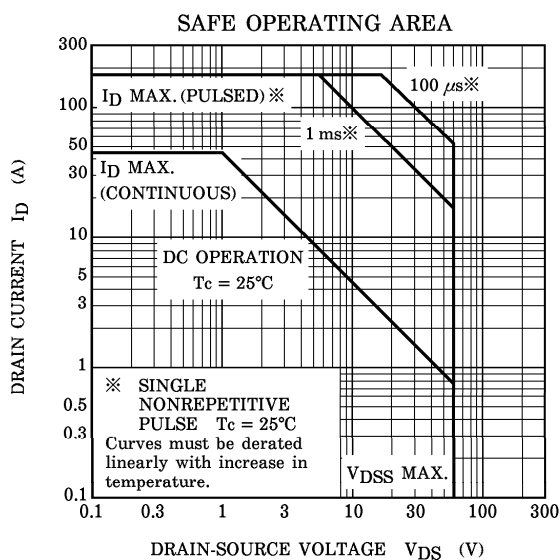
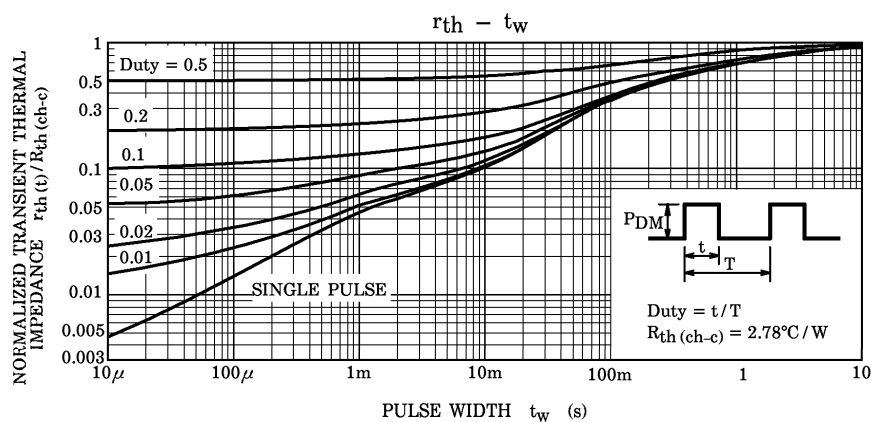


Month (Starting from Alphabet A)

Year (Last Number of the Christian Era)







Peak $I_{AR} = 45 \text{ A}$, $R_G = 25 \Omega$
 $V_{DD} = 25 \text{ V}$, $L = 471 \mu\text{H}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$